

N-Ch MOSFET

Features

30V/40A,

 $R_{DS(ON)} = 10.8 \text{m}\Omega \text{ (max.)} @ V_{GS} = 10 \text{V}$

 $R_{DS(ON)} = 12m\Omega \text{ (max.)} @ V_{GS} = 4.5V$

 $R_{DS(ON)} = 16m\Omega \text{ (max.)} @ V_{GS} = 2.5V$

- 100% UIS+Rg tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

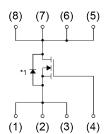
- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.
- Application for NB Adapter in.

Pin Description



DFN5x6A-8_EP

- (1) Source (2) Source (3) Source
- (4) Gate (5) Drain
- (6) Drain
- (7) Drain
- (8) Drain
- *1 Body Diode



Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Symbol	Parameter	Rating	Unit					
Common Ratings								
V _{DSS}	Drain-Source Voltage	30	- v					
V_{GSS}	Gate-Source Voltage	±12						
T _J	Maximum Junction Temperature	150	- °C					
T _{STG}	Storage Temperature Range	-55 to 150						
Is	Diode Continuous Forward Current	T _C =25°C	10					
	Continuous Drain Current	T _C =25°C	40	\Box				
I_D		T _C =100°C	26	$\neg \land$				
I _{DM}	Pulsed Drain Current	T _C =25°C	90					
P _D	Maximum Power Dissipation	T _C =25°C	32	W				
		T _C =100°C	12.8					
$R_{ heta JC}$	Thermal Resistance-Junction to Case	Steady State	3.9	°C/W				
I _D	Continuous Drain Current	T _A =25°C	9					
		T _A =70°C	7	Α				
I_{DM}	Pulsed Drain Current	T _A =25°C	36					
P_D^{a}	Maximum Power Dissipation	T _A =25°C	1.5	W				
		T _A =70°C	1					
$R_{\theta Ja}^{b,c}$	Thermal Resistance-Junction to Ambient	t ≤ 10s	34	°C // //				
		Steady State	84	°C/W				
l _{AS} d	Avalanche Current, Single pulse	L=0.1mH	20	Α				
E _{AS} d	Avalanche Energy, Single pulse	L=0.1mH	20	mJ				

Note a : $R_{\theta JA}$ steady state t=999s.

Note b: t ≤10s and surface mounted on FR-4 board using 1in² pad, 2 oz Cu.

Note c: Steady time = 999s and surface mounted on FR-4 board using 1in² pad, 2 oz Cu.

Note d: UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature T_j=25°C).



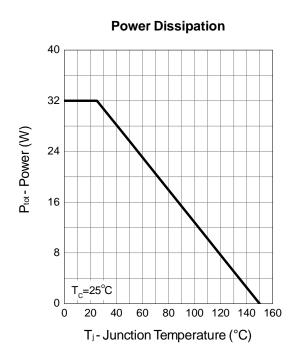
Electrical Characteristics $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

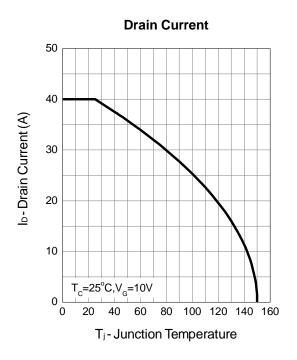
Static Ch		Test Conditions	Min.	Тур.	Max.	Unit			
	Static Characteristics								
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} =0V, I_{DS} =250 μ A	30	-	-	V			
BV_{DSSt}	Drain-Source Breakdown Voltage (transient)	V_{GS} =0V, $I_{D(aval)}$ =20A T_{case} =25°C, $t_{transient}$ =100ns	34	-	-	V			
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V		-	1	μΑ			
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.5	0.85	30 1.3	V			
	Gate Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	0.00	±100	nA			
I _{GSS}	Drain-Source On-state Resistance			9	10.8	- nA			
D e		V _{GS} =10V, I _{DS} =10A	-		10.8				
$R_{DS(ON)}^{e}$		V _{GS} =4.5V, I _{DS} =7A V _{GS} =2.5V, I _{DS} =5A	-	9.6 12	16	mΩ			
Gfs	Forward Transconductance	V _{DS} =25V, I _{DS} =20A	_	45	-	S			
Diode Characteristics V _{DS} =25 V, I _{DS} =20A - 45 - 5									
V _{SD} e	Diode Forward Voltage	I _{SD} =3A, V _{GS} =0V	_	0.75	1.3	V			
t _{rr}	Reverse Recovery Time	ISD-OA, VGS-OV	_	12.2	1.0	ns			
t _a	Charge Time	-		7.5	_				
t _a	Discharge Time	I_{SD} =10A, dI_{SD}/dt =100A/ μ s	_	4.6	-				
Q _{rr}	Reverse Recovery Charge	-	_	5.6	_	nC			
	Characteristics			0.0					
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	2.4	4.3	Ω			
C _{iss}	Input Capacitance		-	1150	1500				
C _{oss}	Output Capacitance	$V_{GS}=0V$, $V_{DS}=15V$,	-	120	-	pF			
C _{rss}	Reverse Transfer Capacitance	Frequency=1.0MHz	-	85	-				
t _{d(ON)}	Turn-on Delay Time		-	9.6	18				
t _r	Turn-on Rise Time	V_{DD} =15V, R_L =15 Ω ,	-	10	18	ns			
t _{d(OFF)}	Turn-off Delay Time	I_{DS} =1A, V_{GEN} =10V, R_{G} =6 Ω	-	29	53				
t _f	Turn-off Fall Time		-	4.5	8				
Gate Cha	rge Characteristics								
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =10V, I _{DS} =10A	-	25.5	36				
Q _g	Total Gate Charge		-	11	12				
Q_{gth}	Threshold Gate Charge	V _{DS} =15V, V _{GS} =4.5V,	-	0.85	-	nC			
Q_{gs}	Gate-Source Charge	I _{DS} =10A	-	2.4	-				
	Gate-Drain Charge	┪	-	3.4	-	1			

Note e : Pulse test ; pulse width≤300µs, duty cycle≤2%.

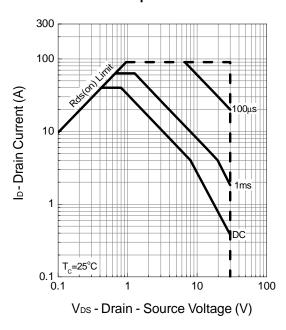


Typical Operating Characteristics

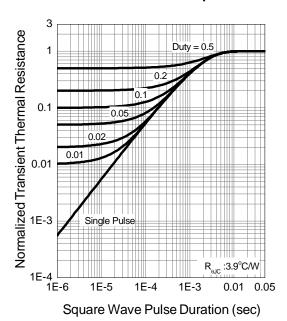




Safe Operation Area



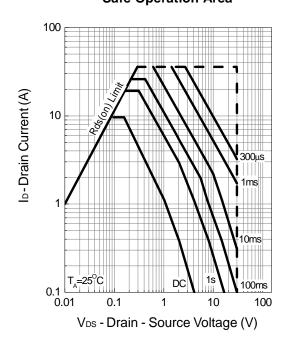
Thermal Transient Impedance



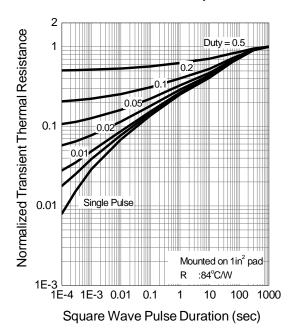


Typical Operating Characteristics (Cont.)

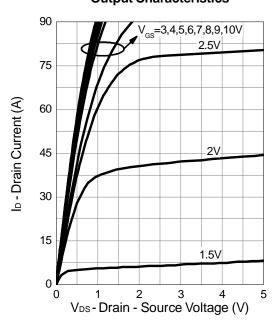
Safe Operation Area



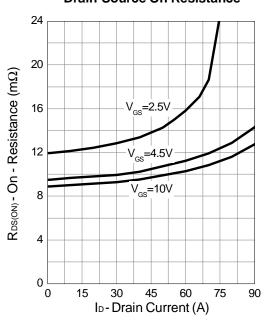
Thermal Transient Impedance



Output Characteristics

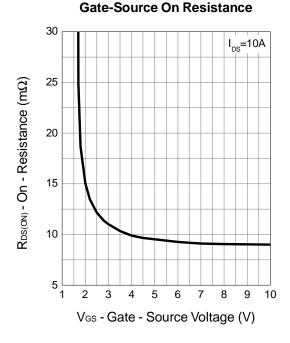


Drain-Source On Resistance

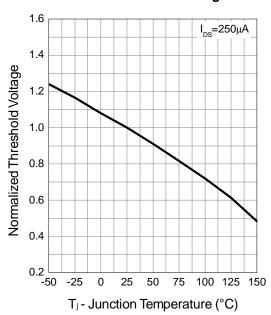




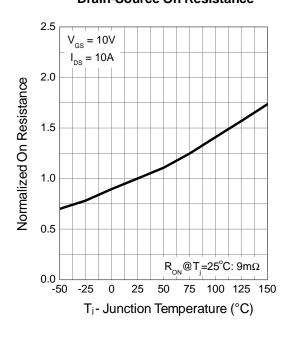
Typical Operating Characteristics (Cont.)



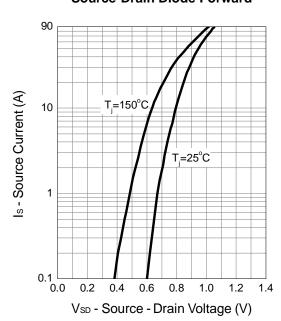
Gate Threshold Voltage



Drain-Source On Resistance

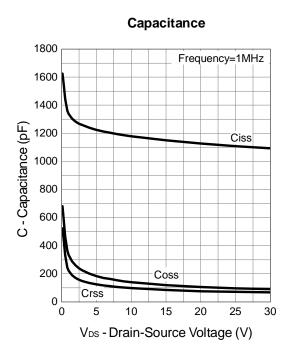


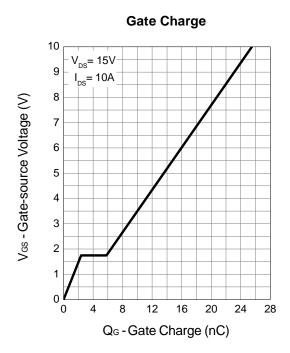
Source-Drain Diode Forward



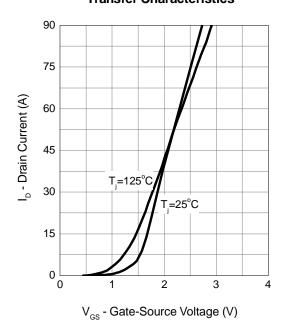


Typical Operating Characteristics (Cont.)



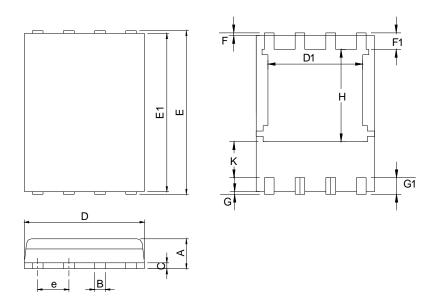


Transfer Characteristics





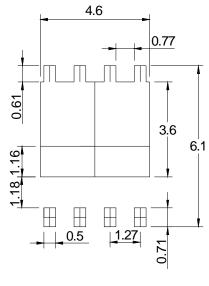
Package Information



Ş	DFN5x6A-8_EP				
SYMBOL	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
Α	0.90	1.20	0.035	0.047	
В	0.3	0.51	0.012	0.020	
С	0.19	0.25	0.007	0.010	
D	4.80	5.30	0.189	0.209	
D1	4.00	4.40	0.157	0.173	
Е	5.90	6.20	0.232	0.244	
E1	5.50	5.80	0.217	0.228	
е	1.27 BSC		0.050 BSC		
F	0.05	0.30	0.002	0.012	
F1	0.35	0.75	0.014	0.030	
G	0.05	0.30	0.002	0.012	
G1	0.35	0.75	0.014	0.030	
Н	3.34	3.9	0.131	0.154	
K	0.762		0.03	-	

Note: 1.Dimension D, D1,D2 and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 10 mil.

RECOMMENDED LAND PATTERN





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